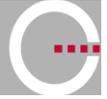


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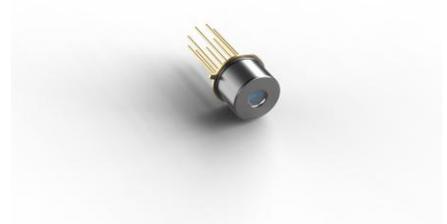
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SINGLE FREQUENCY LASER DFB Laser



General Product Information

Product	Application
780 nm DFB Laser	Spectroscopy (Rb D2 line)
with hermetic 8-Pin TO Package (RoHS compliant)	Metrology
including Monitor Diode, Thermoelectric Cooler and Thermistor	THz Generation



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-40		85
Operational Temperature at Case	T_C	°C	-20		75
Operational Temperature at Chip	T_{chip}	°C	5		50
Forward Current	I_F	mA			200
Reverse Voltage	V_R	V			2
Output Power	P_{opt}	mW			100
TEC Current	I_{TEC}	A			1.0
TEC Voltage	V_{TEC}	V			1.0

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T_{case}	°C	-20		65
Operational Temperature at Chip	T_{chip}	°C	5		45
Forward Current	I_F	mA			180
Output Power	P_{opt}	mW	20		80

Measurement Conditions / Comments

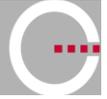
measured by integrated Thermistor

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Characteristics Tchip = 25 °C at BOL

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_C	nm	779	780	781
Target Wavelength	λ_T	nm		780.24	
Linewidth	$\Delta\lambda$	MHz		0.6	1
Mode-hop free Tuning Range	$\Delta\lambda_{\text{tune}}$	pm	25		
Sidemode Suppression Ratio	SMSR	dB	30	45	
Temp. Coefficient of Wavelength	$d\lambda / dT$	nm/K		0.06	
Current Coefficient of Wavelength	$d\lambda / dI$	nm/mA		0.003	
Laser Current	I_{LD}	mA			180
Slope Efficiency	η	mW/mA		0.8	
Threshold Current	I_{th}	mA			70
Divergence parallel	$\Theta_{ }$	°		8	
Divergence perpendicular	Θ_{\perp}	°		21	
Degree of Polarization	DOP	%		90	

Measurement Conditions / Comments
5 ° ... 45 °C at 80 mW
FWHM; Popt = 80 mW
> 10 GHz, at target wavelength
Popt = 80 mW
parallel to Pin 1 - Pin 6 plane (see p. 3)
perpendicular to Pin 1 - Pin 6 plane (see p. 3)
Popt = 80 mW; E field perpendicular to Pin 1 - 6 plane

Monitor Diode

Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	$I_{\text{mon}} / P_{\text{of}}$	μA/mW	0.3		100

Measurement Conditions / Comments
5 V

Thermoelectric Cooler

Parameter	Symbol	Unit	min	typ	max
Current	I_{TEC}	A		0.4	
Voltage	U_{TEC}	V		0.4	
Power Dissipation (total loss at case)	P_{loss}	W		0.4	
Temperature Difference	ΔT	K			40

Measurement Conditions / Comments
Popt = 80 mW, $\Delta T = 20$ K
Popt = 80 mW, $\Delta T = 20$ K
Popt = 80 mW, $\Delta T = 20$ K
Popt = 80 mW, $\Delta T = T_{\text{case}} - T_{\text{chip}} $

Thermistor (Standard NTC Type)

Parameter	Symbol	Unit	min	typ	max
Resistance	R	kΩ		10	
Beta Coefficient	b			3952	
Steinhart & Hart Coefficient A	A			9.531×10^{-4}	
Steinhart & Hart Coefficient B	B			2.644×10^{-4}	
Steinhart & Hart Coefficient C	C			-4.356×10^{-8}	

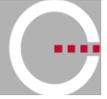
Measurement Conditions / Comments
Tchip = 25 °C
$R_1/R_2 = e^{b(1/T_1 - 1/T_2)}$ at Tchip = 0 ... 50 °C
$1/T = A + B(\ln R) + C(\ln R)^3$
T: Temperature in Kelvin
R: resistance at T in Ω

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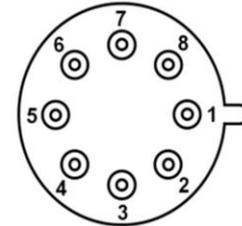
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Pin Assignment

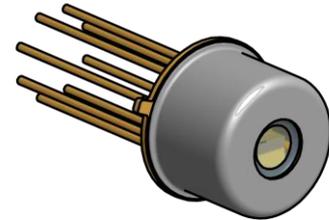
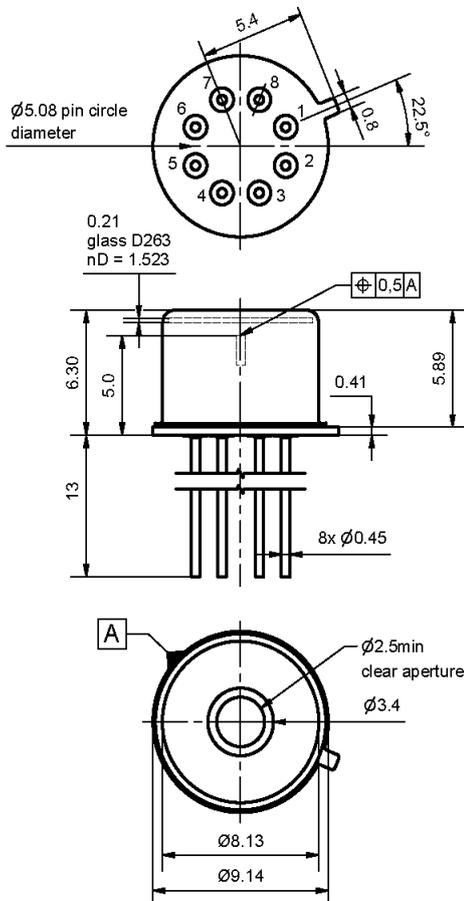
1 Laser Diode Anode	5 Thermistor
2 Laser Diode Cathode	6 Thermistor
3 Thermoelectric Cooler (-)	7 Photo Diode Anode
4 Thermoelectric Cooler (+)	8 Photo Diode Cathode

All 8 pins are isolated from case.



bottom view

Package Drawings



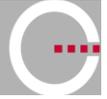
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SINGLE FREQUENCY LASER DFB Laser



Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

A laser diode is sensitive against optical feedback, so an optical isolator may be required in order to avoid any disturbance of the emission spectrum. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.



IEC-60825-1



Complies with 21 CFR 1040.10 and 1040.40